

Pro Electron Surface Mount Bipolar Devices (continued)

Device No. (SOT-23 Mark)	Case Style	V <sub>CE</sub> <sup>*</sup>		V <sub>CE0</sub>		V <sub>EBO</sub>		I <sub>CE</sub> <sup>*</sup>		I <sub>CB</sub>		h <sub>FE</sub>		I <sub>C</sub> & V <sub>CE</sub>		V <sub>CE(SAT)</sub> & V <sub>BE(SAT)</sub>		I <sub>C</sub> @ V <sub>BE(ON)</sub> <sup>*</sup>		C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) @ Min	I <sub>C</sub> (mA)	t <sub>on</sub> (ns) Max	NF (dB) Max	Test Conditions	Process No.
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max							
BSS79C (CF)	TO-236 (49)	60	40	5	50	100	300	150	10	0.4	1.6	0.7	0.85	150	500	6	200	20							19	
BSV52 (B2)	TO-236 (49)	20	12	5	10	25	40	100	10	0.3	1	0.7	0.85	1	10	4	400	10	18					(Note 4)	21 (6-92)	

TEST CONDITIONS

Note 1: I<sub>C</sub> = 200 μA, V<sub>CE</sub> = 5V, f = 1 kHz.  
 Note 2: I<sub>C</sub> = 15 mA, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1 mA.

Note 3: I<sub>CE</sub> = 200 μA, V<sub>CE</sub> = 5V, f = 200 Hz.  
 Note 4: I<sub>C</sub>/I<sub>B</sub> = 3.3.  
 Note 5: I<sub>C</sub> = 10 mA, V<sub>CE</sub> = 3V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1 mA.

Note 6: I<sub>C</sub> = 100 μA, V<sub>CE</sub> = 5V, f = 1 MHz.  
 Note 7: I<sub>C</sub> = 150 mA, V<sub>CE</sub> = 6V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 15 mA.

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device datasheet.